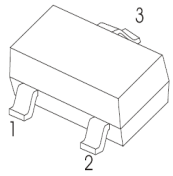
TRANSISTOR (NPN)

SOT－23



1. BASE
2. EMITTER
3. COLLECTOR

FEATURES

- Excellent h_{FE} Linearity
- Switching Applications

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	500	mA
P_C	Collector Power Dissipation	150	mW
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	833	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55～+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=35V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=1V, I_C=100mA	70		400	
	$h_{FE(2)}$	V_{CE}=6V, I_C=400mA	25		70	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100mA, I_B=10mA			0.25	V
Base-emitter voltage	V_{BE}	V_{CE}=1V,I_C=100mA,			1	V
Transition frequency	f_T	V_{CE}=6V,I_C=20mA		300		MHz
Collector output capacitance	C_{ob}	V_{CB}=6V, I_E=0, f=1MHz		7		pF

CLASSIFICATION OF $h_{FE(1)}$, $h_{FE(2)}$

RANK	O	Y	GR(G)
RANGE $h_{FE(1)}$	70－140	120－240	200－400
RANGE $h_{FE(2)}$	25Min	40Min	70Min
MARKING	**WO**	**WY**	**WG**